

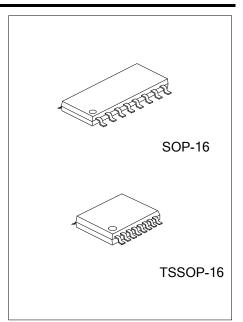
UNISONIC TECHNOLOGIES CO., LTD

UT3232 **CMOS IC Preliminary**

3.0V TO 5.5V LOW POWER **MULTICHANNEL RS-232 LINE** TRANSCEIVERS USING FOR 0.1µF EXTERNAL CAPACITORS

DESCRIPTION

The UTC UT3232 have two receivers and two drivers, and a dual charge-pump circuit. The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3.0V to 5.5V supply. The device operates at data signaling rates up to 250kbit/s and a maximum of 35V/µs driver output slew rate.

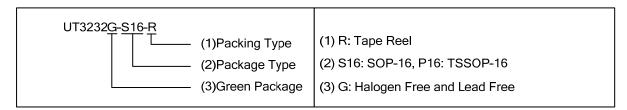


FEATURES

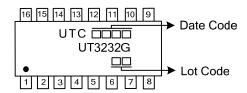
- * Exceeds ±8KV ESD Protection(HBM) for RS-232 I/O Pins
- * Meets the Requirements of TIA/EIA-232-F and ITU V.28 Standards
- * Operates With 3.0V to 5.5V V_{CC} Supply
- * Operates Up To 250kbit/s Data Rate
- * Two Drivers and Two Receivers
- * External Capacitors 4×0.1µF
- * Accepts 5.0V Logic Input With 3.3V Supply

ORDERING INFORMATION

Ordering Number	Package	Packing
UT3232G-S16-R	SOP-16	Tape Reel
UT3232G-P16-R	TSSOP-16	Tape Reel

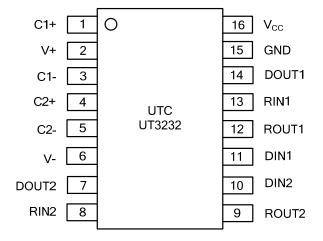


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www.unisonic.com.tw 1 of 7

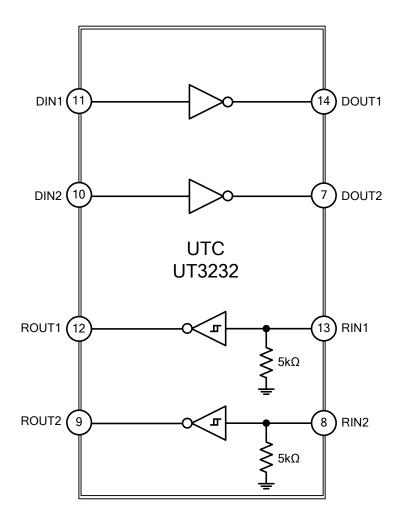
■ PIN CONFIGURATION



■ PIN DESCRIPTION

PIN NO.	PIN NAME	DESCRIPTION
1	C1+	Positive Terminal of Voltage-Doubler Charge-Pump Capacitor
2	V+	+5.5V Generated by the Charge Pump
3	C1-	Negative Terminal of Voltage-Doubler Charge-Pump Capacitor
4	C2+	Positive Terminal of Inverting Charge-Pump Capacitor
5	C2-	Negative Terminal of Inverting Charge-Pump Capacitor
6	V-	-5.5V Generated by the Charge Pump
7	DOUT2	RS-232 Driver Outputs
8	RIN2	RS-232 Receiver Inputs
9	ROUT2	TTL/CMOS Receiver Outputs
10	DIN2	TTL/CMOS Driver Inputs
11	DIN1	TTL/CMOS Driver Inputs
12	ROUT1	TTL/CMOS Receiver Outputs
13	RIN1	RS-232 Receiver Inputs
14	DOUT1	RS-232 Driver Outputs
15	GND	Ground
16	Vcc	+3.0V to +5.5V Supply Voltage

BLOCK DIAGRAM



■ **ABSOLUTE MAXIMUM RATING** [Over operating free-air temperature range (unless otherwise noted)]

PARAMETER		SYMBOL	RATINGS	UNIT
Supply Voltage Range		V_{CC}	-0.3 ~ +6.0	V
Positive Output Supply Voltage Ran	ige (Note 2)	V+	-0.3 ~ +7.0	V
Negative Output Supply Voltage Ra	nge (Note 2)	V-	+0.3 ~ -7.0	V
Supply Voltage Difference (Note 2)		V+ - V-	+13	V
lowet Valtage	Drivers	V	-0.3 ~ +6.0	V
Input Voltage	Receivers	V_{IN}	-25 ~ +25	V
Output Voltage Drivers Receivers		M	-13.2 ~ +13.2	V
		V_{OUT}	-0.3 ~ V _{CC} +0.3	V
Operating Virtual Junction Temperature		T_J	+150	°C
Storage Temperature		T _{STG}	-65 ~ + 150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Lunation to Ambient	SOP-16		105	°C // //
Junction to Ambient	TSSOP-16	θ _{JA}	118	°C/W

■ RECOMMENDED OPERATING CONDITIONS (See Note & Table 1)

PARAMETER	SYMBOL	TEST CC	NDITIONS	MIN	TYP	MAX	UNIT
0		V _{CC} =3.3V		3.0	3.3	3.6	V
Supply Voltage	V _{CC}	V _{CC} =5.0V		4.5	5.0	5.5	V
Driver and Control High-level Input	\/	DIN	V_{CC} =3.3 V	2.0			\/
Voltage	V_{IH}	DIIN	V _{CC} =5.5V	2.4			V
Driver and Control Low-level Input Voltage	V_{IL}	DIN				0.8	V
Driver and Control Input Voltage	V_{IN}	DIN				5.5	V
Receiver Input Voltage	V_{RIN}			-25		25	V
Operating Free-Air Temperature	T_A		·	0		70	°C

Notes: Test conditions are C1~C4=0.1 μ F at V_{CC}=3.3 V±0.3 V; C1=0.047 μ F, C2~C4=0.33 μ F at V_{CC}=5.0 V±0.5 V.

^{2.} All voltages are with respect to network GND.

■ **ELECTRICAL CHARACTERISTICS** [(over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 3 & Table 1)]

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP (Note 1)	MAX	UNIT
Input Leakage Current	I _{IN}	DIN		±0.01	±1	μA
Supply Current	I _{CC}	No load		0.3	1.0	mA
DRIVER SECTION						
High-Level Output Voltage	V_{OH}	DOUT at R_L =3k Ω to GND, DIN=GND	+5.0	+5.4		V
Low-Level Output Voltage	V_{OL}	DOUT at R_L =3k Ω to GND, DIN= V_{CC}	-5.0	-5.4		V
High-Level Input Current	I _{OH}	$V_I = V_{CC}$		±0.01	±1	μΑ
Low-Level Input Current	I_{OL}	V₁ at GND		±0.01	±1	μΑ
Short-Circuit Output Current		V_{CC} =3.6V, V_{OUT} =0V		±35	±60	mA
(Note 2)	I _{OS}	V _{CC} =5.5V, V _{OUT} =0V		±35	±60	mA
Output Resistance	r_{O}	V _{CC} , V+ and V- =0V, V _{OUT} =±2.0V	300	10M		Ω
Output Leakage Current	I_{OFF}	V _{CC} =3.0V~5.5V, V _{OUT} =±12V			±25	μΑ
RECEIVER SECTION						
High-Level Output Voltage	V_{OH}	I _{OH} =-1.0mA	V _{CC} -0.6V	V _{CC} - 0.1V		V
Low-Level Output Voltage	V_{OL}	I _{OL} =1.6mA			0.4	V
Positive-Going Input Threshold	\ /	V _{CC} =3.3V		1.5	2.4	V
Voltage	V_{IT+}	V _{CC} =5.0V		1.8	2.4	V
Negative-Going Input	\/	V _{CC} =3.3V	0.6	1.2		V
Threshold Voltage	V_{IT}	V _{CC} =5.0V	0.8	1.5		V
Input Hysteresis	V_{HYS}	$V_{IT+} \sim V_{IT-}$		0.3		V
Output Leakage Current	I_{OFF}			±0.05	±10	μΑ
Input Resistance	Ri	V _I =±3.0V~±25V	3	5	7	kΩ

Notes: 1. All typical values are at V_{CC} =3.3V or V_{CC} =5.0V, and T_A =25°C.

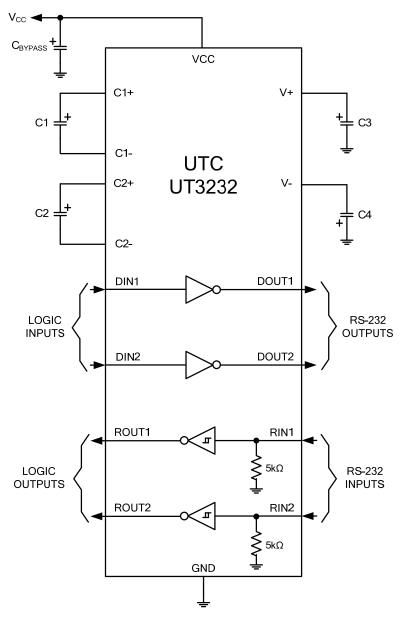
- 2. Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.
- 3. Test conditions are C1~C4=0.1 μ F at V_{CC}=3.3V±0.3V; C1=0.047 μ F, C2~C4=0.33 μ F at V_{CC}=5.0V±0.5V.
- 4. Pulse skew is defined as |t_{PLH}-t_{PHL}| of each channel of the same device.
- **SWITCHING CHARACTERISTICS** [over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 3 and Table 1)]

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP (Note 1)	MAX	UNIT
DRIVER SECTION							
Maximum Data Rate		C_L =1000pF, R_L =3k Ω , One Driver Switching		150	250		Kbit/s
Pulse Skew (Note 4)	t _{SK(p)}	C _L =220pF~250	0pF, R _L =3kΩ~7kΩ		300		ns
Slew Rate, Transition Region $R_L = 3k\Omega \sim 7k\Omega$, $C_L = 220pF \sim 10^{-2}$		$R_L = 3k\Omega \sim 7k\Omega$,	C _L =220pF~1000pF	5		35	1//
		C _L =220pF~2500pF	3		35	V/µs	
RECEIVER SECTION		_					
Propagation Delay Time, Low- to High-Level Output	t _{PLH}	C _L =150pF			300		ns
Propagation Delay Time, Highto Low-Level Output	t _{PHL}	C _L =150pF			300		ns
Output Enable Time	t _{EN}	$C_L=150pF, R_L=3k\Omega$			200		ns
Output Disable Time	t _{DIS}	$C_L=150pF, R_L=3k\Omega$			200		ns
Pulse Skew (Note 4)	t _{SK(P)}	t _{PLH} -t _{PHL}			300		ns

Notes: 1. All typical values are at V_{CC} =3.3V or V_{CC} =5.0V, and T_A =25°C.

- 2. Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.
- 3. Test conditions are C1~C4=0.1 μ F at V_{CC}=3.3V±0.3V; C1=0.047 μ F, C2~C4=0.33 μ F at V_{CC}=5.0V±0.5V.
- 4. Pulse skew is defined as |tplh-tphl| of each channel of the same device.

TYPICAL APPLICATION CIRCUIT



Notes: 1. C3 can be connected to V_{CC} or GND. 2. Resistor values shown are nominal. 3. NC: No internal connection.

- 4. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

Table1. Typical Operating Circuit and Capacitor Values

V _{CC} (V)	C1 (µF)	C2, C3, C4 (µF)	C _{BYPASS} (µF)
3.0~3.6	0.22	0.22	0.22
3.15~3.6	0.1	0.1	0.1
4.5~5.5	0.047	0.33	0.047
3.0~5.5	0.22	1.0	0.22

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